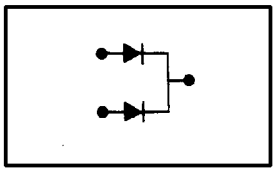
NEW ENGLAND SEMICONDUCTOR

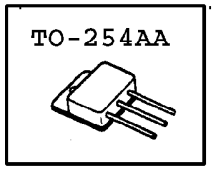
NSG2607

POWER RECTIFIERS

- Schottky Diode - Center Tap
- Low Forward Voltage
- Matched Dual Die Construction
- Epitaxial Construction
- 150°C Operating Temperature

SCHOTTKY BARRIER RECTIFIERS
20 AMPERES





MAXIMUM RATINGS (PER LEG)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100 100	Volts
Average Rectified Forward Current (Rated V_R) T_C = 110°C	$I_{F(AV)}$	20	Amps
Peak Repetitive Forward Current, Per Leg (Rated V_R, Square Wave, 20 kHz) T_C =95°C	I_{FRM}		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	200	Amps
Operating Junction Temperature	T_J	-55 to +150	°C
Storage Temperature	T_{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS			
Thermal Resistance -- Junction to Case	$R_{\theta JC}$	1.3	°C/W
ELECTRICAL CHARACTERISTICS			
Maximum Instantaneous Forward Voltage (1) (I_F = 5 Amps, T_J = 25°C) (I_F = 10 Amps, T_J = 25°C)	V_F	 0.80 0.88	Volts
Maximum Instantaneous Reverse Current (1) (V_R = 80V, T_J = 25°C) (V_R = 80V, T_J = 125°C)	I_R	 35 10	 µA mA
Capacitance/Diode (V_R = 5Vdc TA = 25°C) (100 khz ≤ f ≤ 1 MHz	C_T	800	Pf

(1) Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2.0%

NEW ENGLAND SEMICONDUCTOR
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